



Removal Reaction Mechanisms During Thermal Atomic Layer Etching of Aluminum Oxide: A First-Principles Study

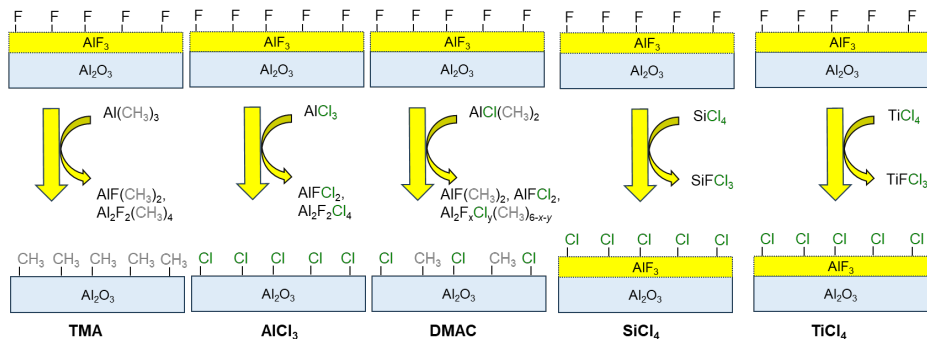
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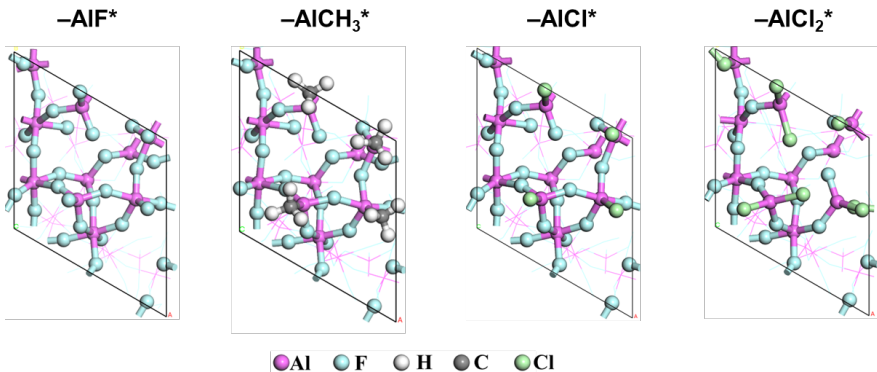
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Summary – Reaction Mechanisms



Amorphous AlF₃ slab models used in this study



Simulation of Removal Reactions

Precursor	Step	Reactions	E _A	ΔG
Al(CH ₃) ₃	1	(AlF) ₃ AlF* + Al(CH ₃) ₃ → (AlF) ₃ AlCH ₃ * + AlF(CH ₃) ₃	0.23	-0.87
	2	(AlF) ₃ AlCH ₃ * + Al(CH ₃) ₃ → -Al + -Al ₂ F + Al ₂ F ₂ (CH ₃) ₄	1.08	-0.85
AlCl ₃	1	(AlF) ₃ AlF* + AlCl ₃ → (AlF) ₃ AlCl* + AlF(CH ₃) ₃	1.00	-0.19
	2	(AlF) ₃ AlCl* + AlCl ₃ → -Al + -Al ₂ F + Al ₂ F ₂ Cl ₄	0.84	-0.51
AlCl(CH ₃) ₂	1a	(AlF) ₃ AlF* + AlCl(CH ₃) ₂ → (AlF) ₃ AlCH ₃ * + AlFClCH ₃	0.17	-0.57
	1b	(AlF) ₃ AlF* + AlCl(CH ₃) ₂ → (AlF) ₃ AlCl* + AlF(CH ₃) ₂	0.15	-0.16
	2a	(AlF) ₃ AlCH ₃ * + AlCl(CH ₃) ₂ → -Al + -Al ₂ F + Al ₂ F ₂ Cl(CH ₃) ₂	0.74	-0.32
	2b	(AlF) ₃ AlCl* + AlCl(CH ₃) ₂ → -Al + -Al ₂ F + Al ₂ FCl ₂ (CH ₃) ₂	0.54	-0.24
SiCl ₄	1	1. (AlF) ₃ AlF* + SiCl ₄ → (AlF) ₃ AlCl* + SiFCl ₃ 2. (AlF) ₃ AlCl* → -Al + -Al ₂ F + AlF ₂ Cl	0.74 1.63	-0.42 0.15
	2	1. (AlF) ₃ AlCl* + SiCl ₄ → (AlF) ₂ (AlCl)AlCl* + SiFCl ₃ 2. (AlF) ₂ (AlCl)AlCl* → -Al + -Al ₂ F + AlFCl ₂	1.06 1.62	-0.41 0.17
	3	1. (AlF) ₂ (AlCl)AlCl* + SiCl ₄ → (AlF)(AlCl) ₂ AlCl* + SiFCl ₃ 2. (AlF)(AlCl) ₂ AlCl* → -Al + -Al ₂ F + AlCl ₃	1.42 0.77	0.29 -0.62
TiCl ₄	1	1. (AlF) ₃ AlF* + TiCl ₄ → (AlF) ₃ AlCl* + TiFCl ₃ 2. (AlF) ₃ AlCl* → -Al + -Al ₂ F + AlF ₂ Cl	0.51 1.63	-0.14 0.15
	2	1. (AlF) ₃ AlCl* + TiCl ₄ → (AlF) ₂ (AlCl)AlCl* + TiFCl ₃ 2. (AlF) ₂ (AlCl)AlCl* → -Al + -Al ₂ F + AlFCl ₂	0.25 1.62	-0.12 0.17
	3	1. (AlF) ₂ (AlCl)AlCl* + TiCl ₄ → (AlF)(AlCl) ₂ AlCl* + TiFCl ₃ 2. (AlF)(AlCl) ₂ AlCl* → -Al + -Al ₂ F + AlCl ₃	0.97 0.77	0.66 -0.62